



ELECTRONICS, INC.

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NTE5005SM thru NTE5031SM Zener Diode, 300mW ±5% Tolerance

Features:

- Zener Voltage 3.3V to 24V
- SOT-23 Type Surface Mount Package

Absolute Maximum Ratings:

Maximum Repetitive Peak Forward Current, I_{FRM}	250mA
Maximum Repetitive Peak Working Current, I_{ZRM}	250mA
Forward Voltage ($I_F = 10mA$, $T_J = +25^\circ C$), V_F	900mV
Total Power Dissipation ($T_A \leq +25^\circ C$, Note 1), P_{tot}	350mW
Maximum Junction Temperature, T_J	+175°C
Storage Temperature Range, T_{stg}	-65° to +175°C

Thermal Characteristics: ($T_J = P \times (R_{thJT} + R_{thSA}) + T_A$)

Thermal Resistance

Junction-to-Tab, R_{thJT}	50K/W
Tab-to-Soldering Points, R_{thTS}	280K/W
Soldering Points-to-Ambient (Note 1), R_{thSA}	90K/W

Note 1. Device mounted on a ceramic substrate of 8mm x 10mm x 0.7mm.

Electrical Characteristics: ($T_J = +25^\circ C$, unless otherwise specified)

NTE Type No.	Nominal Zener Voltage $V_Z @ I_{zt}$	Zener Test Current I_{zt}	Reverse Current $I_R @ V_R$		Typical Differential Resistance $r_{diff} @ I_{zt}$	Typical Temperature Coefficient $S_Z @ I_{zt}$	Typical Diode Capacitance C_d (Note 2)
	V	mA			Ω	mV/K	pF
5005SM	3.3	5	5 μ A	1V	85	-2.4	325
5006SM	3.6	5	5 μ A	1V	85	-2.4	300
5007SM	3.9	5	3 μ A	1V	85	-2.5	300
5008SM	4.3	5	3 μ A	1V	80	-2.5	275
5010SM	5.1	5	2 μ A	2V	40	-0.8	235
5011SM	5.6	5	1 μ A	2V	15	1.2	225
5013SM	6.2	5	3 μ A	4V	10	0.4	185
5014SM	6.8	5	2 μ A	4V	15	1.2	155
5015SM	7.5	5	1 μ A	5V	6	4.0	95
5018SM	9.1	5	500nA	6V	6	5.5	70
5021SM	12.0	5	100nA	0.7 V_{Znom}	10	8.4	65
5024SM	15.0	5	50nA	0.7 V_{Znom}	10	11.4	55
5027SM	18.0	5	50nA	0.7 V_{Znom}	10	14.4	47
5031SM	24.0	5	50nA	0.7 V_{Znom}	25	20.4	33

Note 2. $V_R = 0$, $f = 1MHz$.

